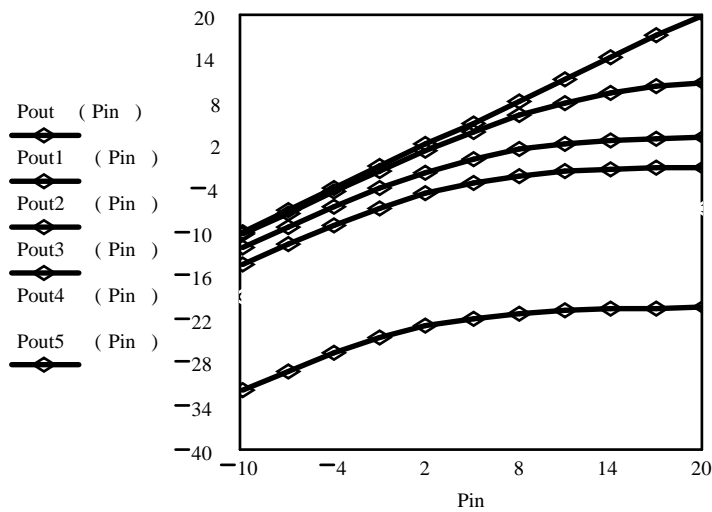


$$\beta^2 = \omega^2 \cdot C \cdot L + \frac{1}{\text{Im}(x)} \cdot \frac{d^2}{dx^2} \text{Im}(x) \quad (5)$$



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539.216.2: 537.633.9

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**COMBINED ANALYSIS OF THE DATA OF STATIC AND DYNAMIC MAGNETIC MEASUREMENTS AS METHOD OF MAGNETIC STATE STUDYING OF CoFeZr/Si MULTILAYER NANOSTRUCTURES**

Last years magnetic nanostructures composed of ferromagnetic metal and semiconductor layers have attracted attention of researchers as promising material for spin electronics devices. These nanostructures may be used for elaboration of the spin field-effect transistors, as well may served as spin-polarized electrons

sources. During deposition of multilayer nanostructures containing Si layers the formation of mixed interface layers is observed. As result the ratio between the thicknesses of magnetic and nonmagnetic layers changes. It means that important applicable magnetoresistive characteristics of nanostructures may change too.

In the frame of studying this problem we have been investigated  $(\text{Co}_{45}\text{Fe}_{45}\text{Zr}_{10}/\text{Si})_{40}$  multilayers deposited by ion beam sputtering [1]. Integrated study of magnetic characteristics of nanostructures using static (vibrating sample magnetometer) and dynamic (ferromagnetic resonance) methods was carried out with the purpose to get information about nanostructure inner state.

The hysteresis loops and the mean saturation magnetization  $I_S^f$  were measured for samples with various ratio  $t_m/t_{\text{Si}}$  of thicknesses of magnetic layers ( $t_m = 1.5 - 3$  nm) and nonmagnetic ones ( $t_{\text{Si}} = 0.5 - 5$  nm). It was found that hysteresis loop parameters depended substantially on the layer thickness and  $I_S^f$  differed from the expected calculated values  $I_S^f(\text{calc})$  - see Fig.1.

From FMR spectra measured with static field applied parallel to the film plane the values of resonance fields  $H_{\text{res}}$  were determined. The effective magnetization values  $M_{\text{eff}}$  were calculated using the Kittel formula [2]:

$$\epsilon_{\text{res}} = \frac{g \cdot \sim B}{h} \sqrt{H_{\text{res}} (H_{\text{res}} + 4fM_{\text{eff}})}$$

where resonance frequency  $\epsilon_{\text{res}} = 9.27$  GHz,  $g$ -factor  $g = 2.15$ ,  $h$  is the Plank's constant,  $\sim B$  is the Bohr magneton.

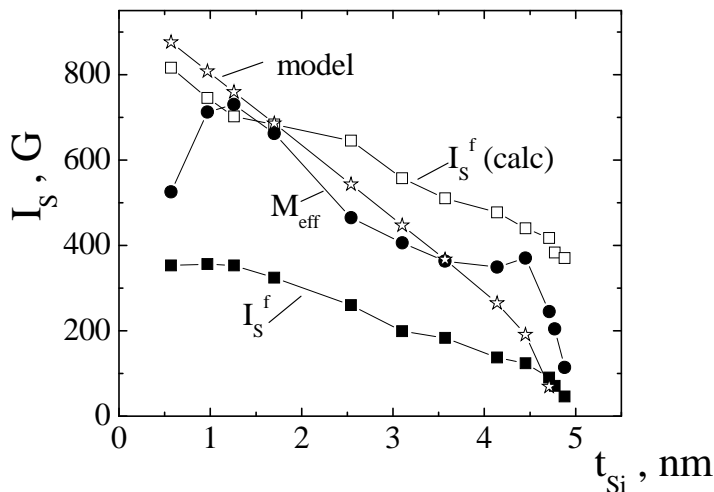


Fig. 1. Dependences of calculated and experimental values of saturation magnetization  $I_S$  versus silicon layer thickness  $t_{\text{Si}}$  for  $(\text{CoFeZr}/\text{Si})_{40}$  nanostructures

